

INFORMATION DISCLOSURE CITATION

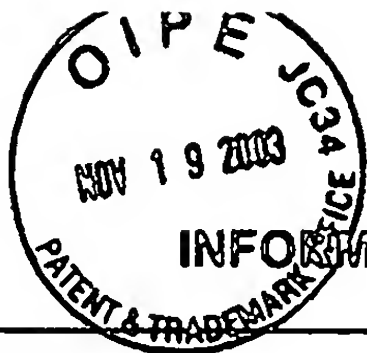
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| Atty. Docket No. | 04329.3139 | Serial No. | |
| Applicant | Mitsuaki IZUHA et al. | | |
| Filing Date | September 12, 2003 | Group: | |

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| | Document Number | Publication Date | Country | Class | Sub Class | Translation Yes or No |
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| Examiner | <i>SR</i> | Date Considered | 12/07/05- |
| *Examiner: | Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. | | |
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OMB No. 0651-0011

INFORMATION DISCLOSURE CITATION

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| Atty. Docket No. | 4329.3139 | Appln. No. | 10/660,555 |
| Applicant | Izuha et al. | | |
| Filing Date | September 12, 2003 | Group: | Unknown |

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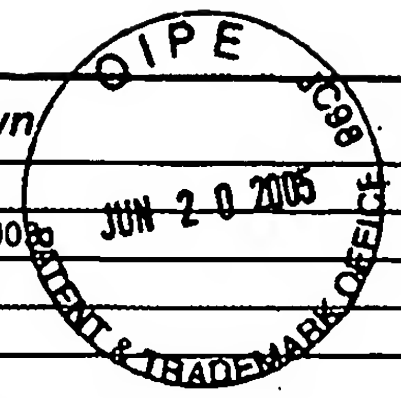
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| IDS Form PTO/SB/08: Substitute for form 1449A/PTO | | | | Complete if Known | |
| INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary) | | | | Application Number | 10/660,555 |
| | | | | Filing Date | September 12, 2005 |
| | | | | First Named Inventor | Mitsuaki Izuha |
| | | | | Art Unit | 2811 |
| | | | | Examiner Name | VU, Quang D. |
| Sheet | 1 | of | 1 | Attorney Docket Number | 4329.3139 |



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Note: Copies of the U.S. Patent Documents are not Required in IDS filed after October 21, 2004

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| | | H. B. Zhao et al., "Interfacial reactions of Ni on Si _{1-x} Ge _x (x=0.2, 0.3) at low temperature by rapid thermal annealing," Journal of Applied Physics, July 1, 2002, Volume 92, Number 1, pp. 214-217. | |
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| Examiner Signature | <i>[Signature]</i> | Date Considered | 12/07/05 |
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